MOS INTEGRATED CIRCUIT μ PD16804

MONOLITHIC H BRIDGE DRIVER CIRCUIT

DESCRIPTION

NEC

The μ PD16804 is a monolithic H bridge driver IC which uses low-ON resistance power MOS FETs in its driver stage. This driver has a forward, reverse, and brake functions and is ideal for the driver circuit of motors for camera that advance or rewind the film, and auto focusing or zooming.

This IC supports a drive current of up to 0.5 A (DC).

FEATURES

High drive current
 IDR = 3 A MAX. at PW ≤ 200 ms (single pulse)

 $I_{DR} = 0.5 A (DC)$

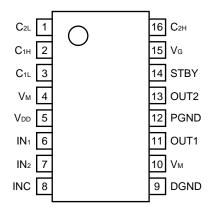
 Low-ON resistance (sum of ON resistances of top and bottom MOS FET)

Ron = 0.6 Ω TYP. at Idr = 0.5 A

- Standby function that turns OFF charge pump circuit
- Compact surface mount package
 16-pin plastic SOP (300 mil)

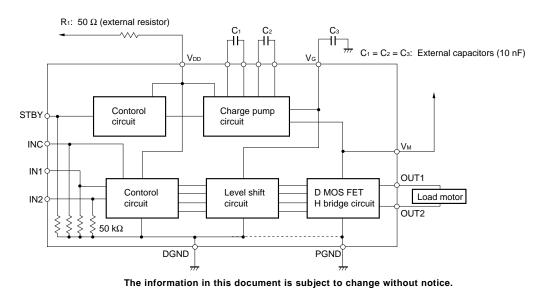
ORDERING INFORMATION

PIN CONFIGURATION (Top View)



Part Number	Package
μPD16804GS	16-pin plastic SOP (300 mil)

BLOCK DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Conditions	Rating	Unit
Supply voltage	Vdd		-0.5 to +6.5/+8.0 ^{Note}	V
	Vм		-0.5 to +6.5/+8.0 ^{Note}	
V _G pin applied voltage	Vg		15	V
Input voltage	Vin		–0.5 to Vdd + 0.5	V
H bridge drive current	IDR1	DC	0.5	А
	Idr2	$PW \le 200 \text{ ms} \text{ (single pulse)}$	3.0	А
Power consumption	Рт	T _A = 25 °C	1.0	W
Operating temperature range	TA		-30 to +60	°C
Operating junction temperature	TJ (MAX)		150	°C
Storage temperature range	Tstg		-55 to +150	°C

Note $\,V_{DD}$ when the charge pump is used/V_{DD} and V_M when V_G is supplied from an external source

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Conditions	Ratings			Unit
Farameter	Symbol	Conditions	MIN.	TYP.	MAX.	Onit
Supply voltage	Vdd	During normal operation			6.0/7.5 ^{Note 2}	V
		All input pins are low	2.5			
	Vм		0.5		7.5	V
Charge pump capacitance	C1 to C3			10		nF
V _G pin applied voltage ^{Note 1}	Vg		11		14	V
Operating temperature	TA	Ambient temperature	-30		60	°C

Notes 1. When a voltage is applied from an external source to the $\ensuremath{\mathsf{V}}\xspace{\mathsf{g}}$ pin

2. When the charge pump is used/when $\ensuremath{\mathsf{V}}\xspace{\mathsf{G}}$ is supplied from an external source

ELECTRICAL SPECIFICATIONS (Unless otherwise specified, $T_A = 25$ °C, $V_{DD} =$ recommended operating condition, $V_M = 0.5$ to 7.5 V)

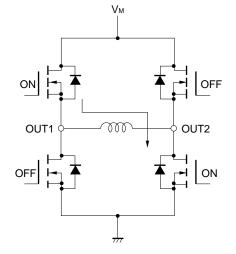
Descention	Cumbal	Quantitie and	Ratings			
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V _{DD} pin current	pin current IDD1 VDD = 5 V, TA = recommended conditions Control pins at high level			0.6	2.0	mA
	Idd2	V _{DD} = 5 V, T _A = recommended conditions Control pins at low level		0.3	10	μA
V _M pin current	Im1	Control pins at low level T _A = recommended conditions		0.1	10	μΑ
	Ім2	Control pins at low level			1.0	μΑ
H bridge ON resistance ^{Note}	Ron	Idr = 0.5 A, Vdd = Vm = 5 V		0.6	0.8	Ω
Control pin high-level input voltage	Vін	T _A = recommended condition	$V_{\text{DD}} \times 0.6$			V
Control pin low-level input voltage	Vil	T _A = recommended condition			$V_{\text{DD}} \times 0.2$	V
Charge pump circuit turn-ON time	t ong	$V_{DD} = V_M = 5 V,$		0.5	1.0	ms
H bridge output circuit turn-ON time	tолн	T _A = recommended conditions			10	μs
H bridge output circuit turn-OFF time	toffh	$C_1 = C_2 = C_3 = 10 \text{ nF}$ IDR = 0.5 A			5.0	μs
Control pin input pull-down resistor	RIND		35	50	65	kΩ
		T _A = recommended condition	25		75	kΩ

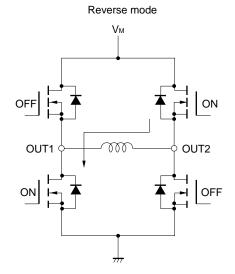
Note Sum of ON resistances of top and bottom MOS FETs

FUNCTION TABLE

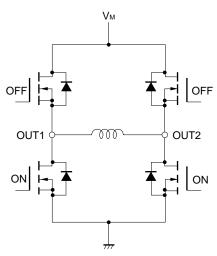
Input Signal			Function			
IN1	IN2	INC	STB	Function		
н	L	Н	н	Forward mode		
L	Н	Н	н	Reverse mode		
Н	Н	Н	Н	Brake mode		
L	L	Н	н	Stop mode		
×	×	L	н	Stop mode		
×	×	×	L	Standby mode		

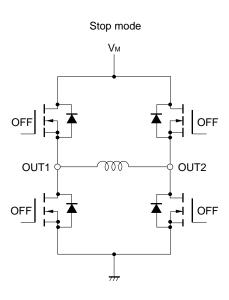
Forward mode

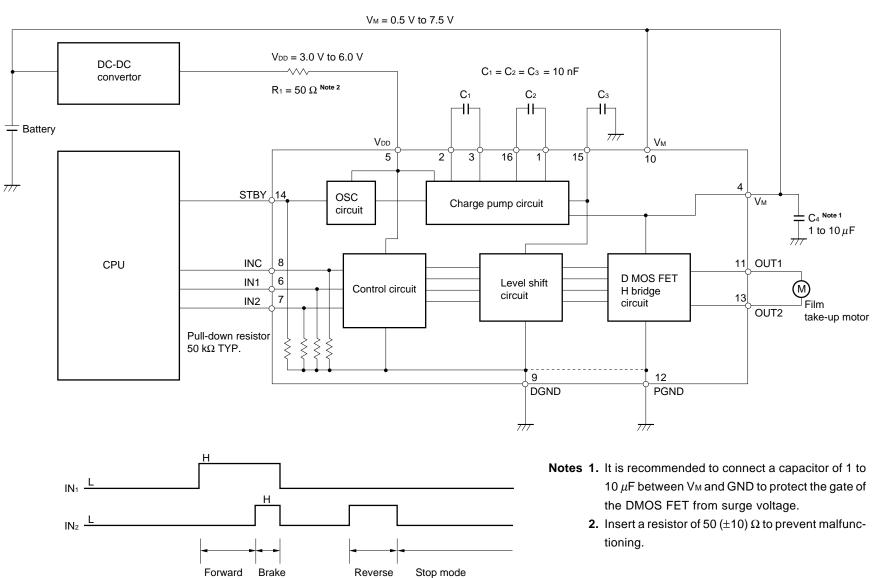




Brake mode







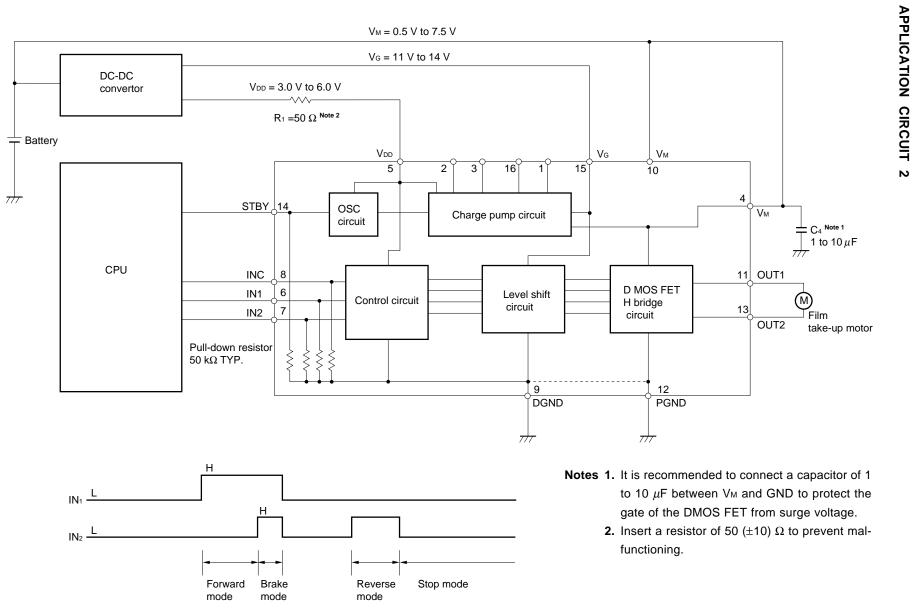
APPLICATION CIRCUIT 1

С

mode

mode

mode

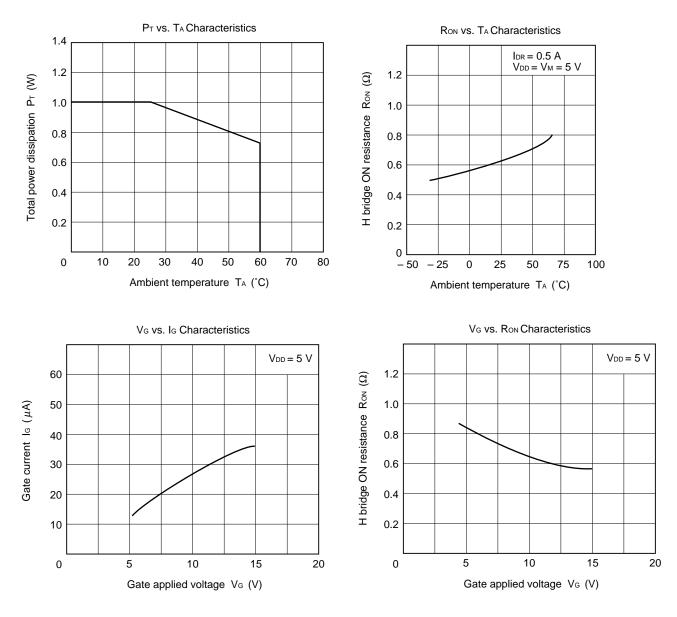




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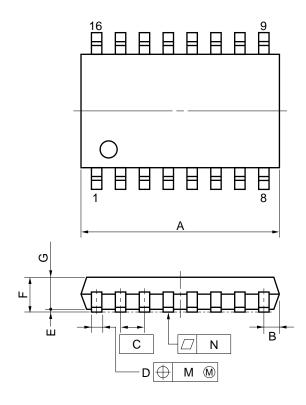
 μ PD16804

TYPICAL CHARACTERISTICS (TA = 25 $^{\circ}$ C)

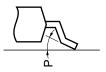


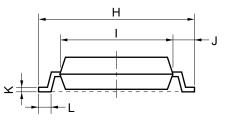
PACKAGE DIMENSION

16 PIN PLASTIC SOP (300 mil)



detail of lead end





NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
А	10.46 MAX.	0.412 MAX.
В	0.78 MAX.	0.031 MAX.
С	1.27 (T.P.)	0.050 (T.P.)
D	$0.40^{+0.10}_{-0.05}$	$0.016\substack{+0.004\\-0.003}$
Е	0.1±0.1	0.004±0.004
F	1.8 MAX.	0.071 MAX.
G	1.55	0.061
н	7.7±0.3	0.303±0.012
I	5.6	0.220
J	1.1	0.043
к	$0.20^{+0.10}_{-0.05}$	$0.008^{+0.004}_{-0.002}$
L	0.6±0.2	$0.024^{+0.008}_{-0.009}$
М	0.12	0.005
Ν	0.10	0.004
Р	3° ^{+7°} 3°	3° ^{+7°} -3°
		216GM-50-300B-/

P16GM-50-300B-4

RECOMMENDED SOLDERING CONDITIONS

It is recommended to solder this product under the conditions described below. For soldering methods and conditions other than those listed below, consult NEC.

Surface mount type

For the details of the recommended soldering conditions of this type, refer to **Semiconductor Device Mounting Technology Manual (C10535E)**.

μ PD16804GS

Soldering Method	Soldering Conditions	Symbol of Recommended Soldering
Infrared reflow	Peak package temperature: 235 °C, Time: 30 seconds MAX. (210 °C MIN.), Number of times: 2 MAX.	IR35-00-2
VPS	Peak package temperature: 215 °C, Time: 40 seconds MAX. (200 °C MIN.), Number of times: 2 MAX.	VP15-00-2
Wave soldering	Soldering bath temperature: 260 °C Time: 10 seconds MAX., Preheating temperature: 120 °C MAX. (package surface temperature), Number of times: 1	WS60-00-1

Note The number of storage days at 25 °C, 65% RH after the dry pack has been opened

Caution Do not use two or more soldering methods in combination (except pin partial heating).

[MEMO]

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Anti-radioactive design is not implemented in this product.